

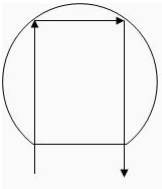
Part Number

Customer

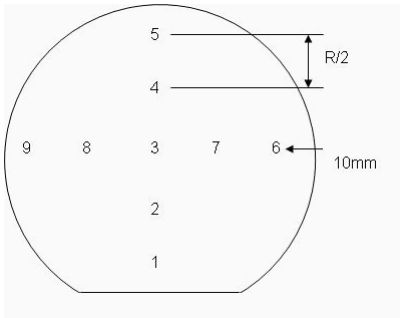
Category	Parameter	Specification	Measurement Method
OverallWafer	1.0 Diameter	200.00 +/- 0.20 mm	
	2.0 Notch Direction	{110} +/- 0.5 degree	Wafer Vendor
	3.0 Notch or Flat	Notch	Wafer Vendor
	4.0 Secondary Flat Orientation	none	
	5.0 Overall Thickness	500.00 +/- 5.00 μ m	ADE, 100%
	6.0 Total Thickness Variation (TTV)	<3.00 μ m	Guaranteed by Process
	7.0 Bow	<40.00 μ m	ADE to ASTM F534, 20%
	8.0 Warp	<40.00 μ m	ADE to ASTM F657, 20%
	9.0 Edge Chips	0	Bright Light, 100% (note 2)
	10.0 Edge Exclusion	5mm	
HandleSilicon	11.0 Handle Growth Method	CZ	Wafer Vendor
	12.0 Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	13.0 Handle Thickness	500.00 +/- 5.00 μ m	ADE, 100%
	14.0 Handle Doping Type	P	Wafer Vendor
	15.0 Handle Dopant	Boron	Wafer Vendor
	16.0 Handle Resistivity	1 ~ 50 Ohmcm	Wafer Vendor
	17.0 Backside Finish	Polished with light handling marks & lasermarking	Wafer Vendor
	18.0 Total scratch length	Front side - 10mm total accumulated length.	Bright Light, 100% (note 2)
	19.0 Surface Haze	Front side - None	Bright Light, 100% (note 2)
OverallWafer	20.0 LPDs > 0.3 μ m	<60 count >0.3 μ m diameter.	Tencor Particle counter

Part Number	Customer
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Category	Parameter	Specification	Measurement Method
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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 200.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information